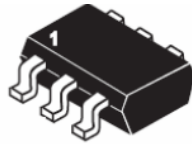
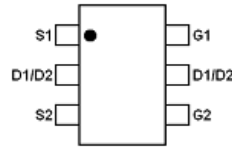
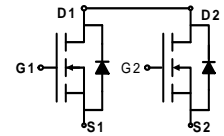


Main Product Characteristics:

V_{DSS}	20V
$R_{DS(on)}$	14.7m Ω (typ.)
I_D	6A


SOT23-6

**Marking and pin
Assignment**

Schematic diagram
Features and Benefits:

- Advanced trench MOSFET process technology
- Special designed for battery protection, load switching and general power management
- Ultra low on-resistance with low gate charge
- Fast switching and reverse body recovery
- 150°C operating temperature


Description:

It utilizes the latest trench processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in battery protection, power switching application and a wide variety of other applications

Absolute max Rating:

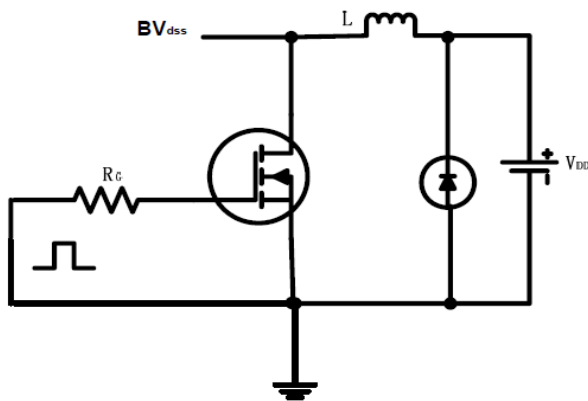
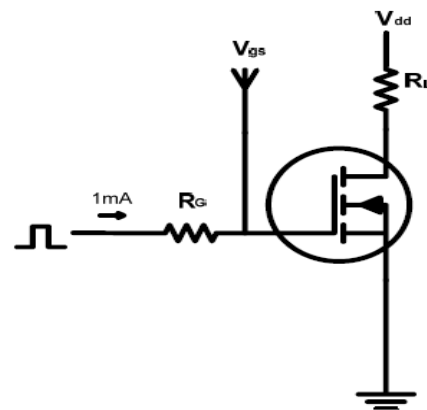
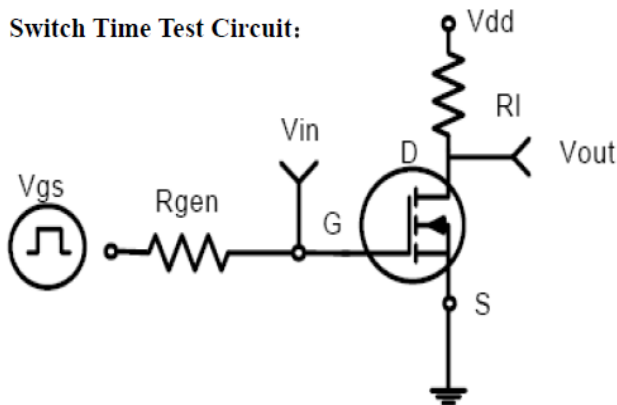
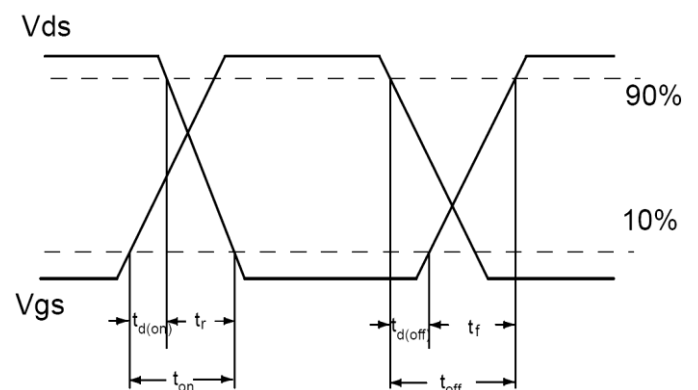
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous@ Current-Pulsed (Note 1)	I_D	6	A
	I_{DM}	25	A
Maximum Power Dissipation	P_D	1.4	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^{\circ}C$

Thermal Resistance

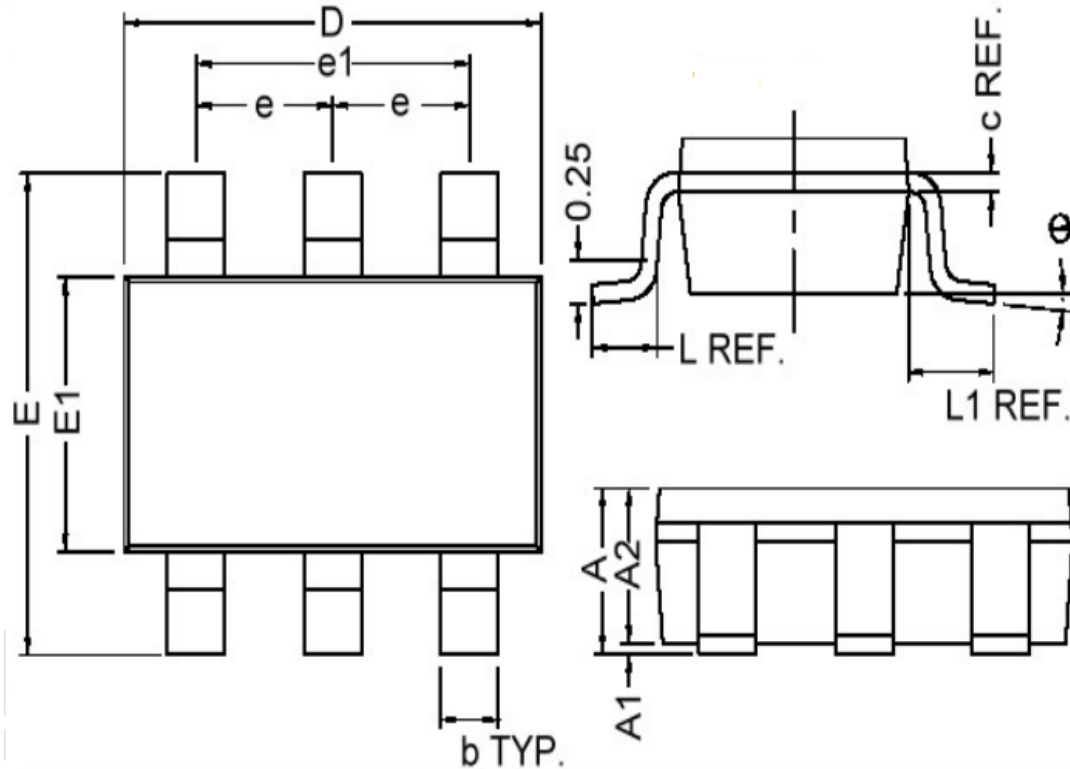
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	100	$^{\circ}C/W$
--	-----------------	-----	---------------

Electrical Characterizes @ $T_A=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=16V, V_{GS}=0V$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$			± 100	nA
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.6		1.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=4.5V, I_D=6A$		14.7	20	m Ω
		$V_{GS}=2.5V, I_D=5.2A$		18.8	25	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=6A$		22		S
DYNAMIC CHARACTERISTICS (Note4)						
Input Capacitance	C_{ISS}	$V_{DS}=8V, V_{GS}=0V,$ $F=1.0\text{MHz}$		600		PF
Output Capacitance	C_{OSS}			315		PF
Reverse Transfer Capacitance	C_{RSS}			135		PF
SWITCHING CHARACTERISTICS (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, I_D=1A$ $V_{GS}=4.5V, R_{GEN}=6\Omega$		11		nS
Turn-on Rise Time	t_r			12		nS
Turn-Off Delay Time	$t_{d(off)}$			35		nS
Turn-Off Fall Time	t_f			30		nS
Total Gate Charge	Q_g	$V_{DS}=10V, I_D=6A,$ $V_{GS}=4.5V$		5		nC
Gate-Source Charge	Q_{gs}			1.2		nC
Gate-Drain Charge	Q_{gd}			2		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=2A$		0.8	1.2	V
Diode Forward Current (Note 2)	I_S				1.7	A

Test circuits and Waveforms
EAS test circuits:

Gate charge test circuit:

Switch Time Test Circuit:

Waveforms:

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production testing.

Mechanical Data:
SOT23-6 Dimensions in Millimeters (UNIT:mm)


REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	1.10 MAX.		L	0.45 REF.	
A1	0	0.10	L1	0.60 REF.	
A2	0.70	1.00	θ	0°	10°
c	0.12 REF.		b	0.30	0.50
D	2.70	3.10	e	0.95 REF.	
E	2.60	3.00	e1	1.90 REF.	
E1	1.40	1.80			

ATTENTION:

- Any and all Silikron products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your Silikron representative nearest you before using any Silikron products described or contained herein in such applications.
- Silikron assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all Silikron products described or contained herein.
- Specifications of any and all Silikron products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- Silikron Semiconductor CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all Silikron products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of Silikron Semiconductor CO.,LTD.
- Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. Silikron believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the Silikron product that you intend to use.
- This catalog provides information as of Dec, 2008. Specifications and information herein are subject to change without notice.

Customer Service**Worldwide Sales and Service:**

Sales@silikron.com

Technical Support:

Technical@silikron.com

Suzhou Silikron Semiconductor Corp.

501, NW-20, Nanopolis, 99th Jinjihu Avenue, Industrial Park, Suzhou, P.R, China

TEL: (86-512) 62560688

FAX: (86-512) 62560688-8092

E-mail: Sales@silikron.com